

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary) PTO Form 1449				Attorney Docket No. 040894-7183		Application No.: 10/525,045	
				Applicants: Shigeki SAKAI		PAGE 1 of 1	
				Filing Date: February 18, 2005		Group Art Unit: Unassigned	

U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Sub Class	Filing Date	
MDH	6,060,755	May 9, 2000	Ma et al.	-	-		
↓	2003/0027360 A1	Feb. 6, 2003	Hsu et al.	-	-		

FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Sub Class	Translation YES NO	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
MDH	Hag-Ju CHO, et al., "Structural and Electrical Properties of HfO ₂ With Top Nitrogen Incorporated Layer", <i>IEEE Electron Device Letters</i> , Vol. 23, No. 5, May 2002, pages 249-251.
↓	Hoon Sang CHOI, et al., "Electrical Characteristics of Pt/SrBi ₂ Ta ₂ O ₇ /Si Using Ta ₂ O ₅ as the Buffer Layer", <i>2001 The Japan Society of Applied Physics, Jpn. J. Appl. Phys. Vol. 40 (2001), Part 1, No. 4B, April 2001, pages 2940-2942</i>
↓	Kyu-Jeong CHOI, et al., "Metal/ferroelectric/insulator/semiconductor structure of Pt/Sr Bi ₂ Ta ₂ O ₇ /YMnO ₃ /Si using YMnO ₃ as the buffer layer", <i>1999 American Institute of Physics, Applied Physics Letters</i> , Vol. 75, No. 5, August 2, 1999, pages 722-724.
↓	C. H. CHOI, et al., "Thermally Stable CVD HfO _x N _y Advanced Gate Dielectrics with Poly-Si Gate Electrode", <i>2002 IEEE, IEDM</i> , pages 857-860.

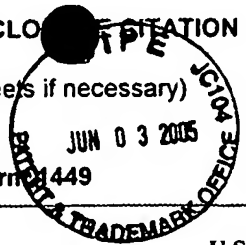
Examiner <i>Marc D Ham</i>	Date Considered <i>8/31/06</i>
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INFORMATION DISCLOSURE CITATION

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PTO Form 1449



Attorney Docket No.
040894-7183

Application No.:
10/525,0452

Applicant(s): Shigeki SAKAI

PAGE 1 of 1

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Group Art Unit: 5664

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*Examiner Initial	Document Number	Date	Name	Class	Sub Class	Filing Date

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Document Number	Date	Country	Class	Sub Class	Translation YES NO	
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↓	Shinji Migita et al., "Fabrication and Electrical Properties of Ferroelectric-gate FET with Epitaxial Gate Structure," <i>Denshi Jōhō Tūshin Gakkai Ronbun-shi</i> , Vol. J85-C, No. 1 (January 2002 issue), pp. 14-22.

Examiner

Imperio D. Harrison

Date Considered

8/31/06

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